



SLLS174G-FEBRUARY 1994-REVISED APRIL 2009

SN55LBC180 SN65LBC180

SN75LBC180

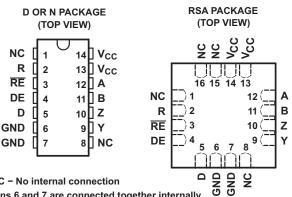
LOW-POWER RS-485 LINE DRIVER AND RECEIVER PAIRS

FEATURES

- Designed for High-Speed Multipoint Data Transmission Over Long Cables
- Operate With Pulse Durations as Low as 30 ns
- Low Supply Current . . . 5 mA Max •
- Meet or Exceed the Requirements of ANSI . Standard RS-485 and ISO 8482:1987(E)
- 3-State Outputs for Party-Line Buses
- Common-Mode Voltage Range of –7 V to 12 V •
- **Thermal Shutdown Protection Prevents Driver Damage From Bus Contention**
- Positive and Negative Output Current Limiting
- Pin Compatible With the SN75ALS180

DESCRIPTION

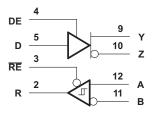
The SN55LBC180, SN65LBC180 and SN75LBC180 differential driver and receiver pairs are monolithic integrated circuits designed for bidirectional data communication over long cables that take on the characteristics of transmission lines. They are balanced, or differential, voltage mode devices that meet or exceed the requirements of industry standards ANSI RS-485 and ISO 8482:1987(E). These devices are designed using TI's proprietary LinBiCMOS[™] with the low-power consumption of CMOS and the precision and robustness of bipolar transistors in the same circuit.



NC - No internal connection

Pins 6 and 7 are connected together internally Pins 13 and 14 are connected together internally

logic diagram (positive logic)



T _A	PACKAGE	PART NUMBER	PART MARKING					
	PDIP	SN75LBC180N	SN75LBC180N					
0°C to 70°C	SOIC	SN75LBC180D	7LB180					
	QFN	SN75LBC180RSA	LB180					
	PDIP	SN65LBC180N	65LBC180N					
-40°C to 85°C	SOIC	SN65LBC180D	6LB180					
	QFN	SN65LBC180RSA	BL180					
-55°C to 125°C	QFN	SN55LBC180RSA	SN55LBC180					

ORDERING INFORMATION



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. LinBiCMOS is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION (CONTINUED)

The SN55LBC180, SN65LBC180 and SN75LBC180 combine a differential line driver and receiver with 3-state outputs and operate from a single 5-V supply. The driver and receiver have active-high and active-low enables, respectively, which can be externally connected to function as a direction control. The driver differential outputs and the receiver differential inputs are connected to separate terminals for full-duplex operation and are designed to present minimum loading to the bus whether disabled or powered off ($V_{CC} = 0$). These parts feature a wide common-mode voltage range making them suitable for point-to-point or multipoint data-bus applications.

The devices also provide positive and negative output-current limiting and thermal shutdown for protection from line fault conditions. The line driver shuts down at a junction temperature of approximately 172°C.

The SN75LBC180 is characterized for operation over the commercial temperature range of 0°C to 70°C. The SN65LBC180 is characterized over the industrial temperature range of –40°C to 85°C.

The SN55LBC180 is characterized for operation over the military temperature range of -55°C to 125°C.

DRIVER								
INPUT	ENABLE	OUTPUTS						
D	DE	Y	Z					
Н	Н	Н	L					
L	н	L	Н					
X	L	Z	Z					
RECEIVER								
DIFFERENTIAL INPUTS A-B	EN <u>AB</u> LE RE	OUTF R	TUY					
V _{ID} ≥ 0.2 V	L	Н						
$-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$	L	?						
$V_{ID} \le -0.2 V$	L	L						
Х	Н	Z						
Open circuit	L	Н						

FUNCTION TABLES⁽¹⁾

 (1) H = high level, L = low level, ? = Indeterminate, X = irrelevant, Z = high impedance (off)

2



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

				UNIT		
V _{CC}	Supply voltage range (2)		-0.3 to 7	V		
V _{BUS}	Bus voltage range (A, B,	Y, Z) ⁽²⁾	-10 to 15	V		
	Voltage range at D, R, DI	E, RE ⁽²⁾	–0.3 to V _{CC} + 0.5			
	Continuous total power di	ssipation ⁽³⁾	Internally limited			
	Total power dissipation		See Dissipation Rating Table			
T _{stg}	Storage temperature rang	je	-65 to 150	°C		
I _O	Receiver output current ra	ange	-50 to 50	mA		
		HBM (Human Body Model) EIA/JESD22-A114	±4	kV		
ESD	Electrostatic discharge	MM (Machine Model) EIA/JESD22-A115	400	V		
		CDM (Charge Device Model) EIA/JESD22-C101	1.5	kV		

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to GND.

(3) The maximum operating junction temperature is internally limited. Use the dissipation rating table to operate below this temperature.

DISSIPATION RATING TABLE

PACKAGE ⁽¹⁾	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	_
Ν	1150 mW	9.2 mW/°C	736 mW	598 mW	_
RSA	3333 mW	26.67 mW/°C	2133 mW	1733 mW	400 mW

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT	
V _{CC}	Supply voltage		4.75	5	5.25	V	
V _{IH}	High-level input voltage	D, DE, and RE	2			V	
V _{IL}	Low-level input voltage	D, DE, and RE			0.8	V	
V _{ID}	Differential input voltage		-6 ⁽¹⁾		6	V	
$V_{O}, V_{I}, \text{ or } V_{IC}$	Voltage at any bus terminal (separately or common mode)	A, B, Y, or Z	-7 ⁽¹⁾		12	V	
	High-level output current	Y or Z			-60		
I _{OH}		R			-8	mA	
1		Y or Z			60	~^^	
IOL	Low-level output current	R			8	mA	
		SN55LBC180	-55		125		
T _A	Operating free-air temperature	SN65LBC180	-40		85	°C	
		SN75LBC180	0		70	l	

(1) The algebraic convention where the least positive (more negative) limit is designated minimum, is used in this data sheet for the differential input voltage, voltage at any bus terminal, operating temperature, input threshold voltage, and common-mode output voltage.



DRIVER SECTION

ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IK}	Input clamp voltage	I _I = -18 mA				-1.5	V
			SN55LBC180	1	2.5	5	
		$R_L = 54 \Omega$, See Figure 1	SN65LBC180	1.1	2.5	5	
	Differential extruct valtage magnitude (2)	coo riguro r	SN75LBC180	1.5	2.5	5	V
V _{OD}	Differential output voltage magnitude ⁽²⁾	$R_L = 60 \Omega$, See Figure 2	SN55LBC180	1	2.5	5	v
			SN65LBC180	1.1	2	5	
			SN75LBC180	1.5	2	5	
Δ V _{OD}	Change in magnitude of differential output voltage ⁽³⁾	See Figure 1 and F			±0.2	V	
V _{OC}	Common-mode output voltage			1	2.5	3	V
Δ V _{OC}	Change in magnitude of common-mode output voltage ⁽³⁾	$R_L = 54 \Omega,$	See Figure 1			±0.2	V
lo	Output current with power off	$V_{CC} = 0,$	$V_0 = -7 V$ to 12 V			±100	μΑ
I _{OZ}	High-impedance-state output current	$V_0 = -7$ V to 12 V				±100	μΑ
I _{IH}	High-level input current	V _I = 2.4 V				100	μΑ
IIL	Low-level input current	$V_{I} = 0.4 V$				100	μA
I _{OS}	Short-circuit output current	$-7 \text{ V} \leq \text{V}_0 \leq 12 \text{ V}$				±250	mA
		Receiver disabled	Outputs enabled			5	mA
I _{CC}	Supply current		Outputs disabled			3	ШA

(1) All typical values are at V_{CC} = 5 V and T_A = 25°C.

The minimum V_{OD} specification may not fully comply with ANSI RS-485 at operating temperatures below 0°C. System designers should (2)

take the possibly lower output signal into account in determining the maximum signal-transmission distance. $\Delta |V_{OD}|$ and $\Delta |V_{OC}|$ are the changes in the steady-state magnitude of V_{OD} and V_{OC} , respectively, that occur when the input is changed (3) from a high level to a low level.

SWITCHING CHARACTERISTICS

 $V_{CC} = 5 \text{ V}, \text{ } \text{T}_{A} = 25^{\circ}\text{C}$

	PARAMETER		TEST CONDITIONS		TYP	MAX	UNIT
t _{d(OD)}	Differential output delay time	P - 54 0	Soo Figuro 2	7	12	18	ns
t _{t(OD)}	Differential output transition time	$R_L = 54 \Omega,$	See Figure 3	5	10	20	ns
t _{PZH}	Output enable time to high level	$R_L = 110 \Omega$,	See Figure 4			35	ns
t _{PZL}	Output enable time to low level	R _L = 110 Ω,	See Figure 5			35	ns
t _{PHZ}	Output disable time from high level	$R_L = 110 \Omega$,	See Figure 4			50	ns
t _{PLZ}	Output disable time from low level	$R_L = 110 \Omega$,	See Figure 5			35	ns

SWITCHING CHARACTERISTICS (SN55LBC180)

 $V_{CC} = 5 \text{ V}, \text{ } \text{T}_{A} = 25^{\circ}\text{C}$

4

	PARAMETER		TEST CONDITIONS		MAX	UNIT	
t _{d(OD)}	Differential output delay time	D 54.0	$R_L = 54 \Omega$, See Figure 3			ns	
t _{t(OD)}	Differential output transition time	$R_{L} = 54 \Omega,$				ns	
t _{PZH}	Output enable time to high level	D 110 0	See Figure 4	32		~~	
t _{PHZ}	Output disable time from high level	R _L = 110 Ω,	See Figure 4	55		ns	
t _{PZL}	Output enable time to low level	D 110 0	Soo Figuro F	32			
t _{PLZ}	Output disable time from low level	$R_L = 110 \Omega$,	$R_L = 110 \Omega$, See Figure 5			ns	



RECEIVER SECTION

ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT	
V_{IT+}	Positive-going input threshold voltage	I _O = -8 mA				0.2	V	
$V_{\text{IT}-}$	Negative-going input threshold voltage	I _O = 8 mA		-0.2			V	
V_{hys}	Hysteresis voltage (V _{IT+} – V _{IT–})				45		mV	
V _{IK}	Enable-input clamp voltage	I _I = -18 mA		-1.5			V	
V _{OH}	High-level output voltage	V _{ID} = 200 mV,	I _{OH} = -8 mA	3.5	4.5		V	
V _{OL}	Low-level output voltage	$V_{ID} = -200 \text{ mV},$	I _{OL} = 8 mA		0.3	0.5	V	
I _{OZ}	High-impedance-state output current	$V_{O} = 0 V$ to V_{CC}				±20	μA	
I _{IH}	High-level enable-input current	V _{IH} = 2.4 V		-50			Α	
IIL	Low-level enable-input current	V _{IL} = 0.4 V		-100			μA	
		$V_{I} = 12 V, V_{CC} = 5 V,$	Other input at 0 V		0.7	1		
		V _I = 12 V, V _{CC} = 0 V,	Other input at 0 V		0.8	1		
II	Bus input current	$V_{I} = -7 V, V_{CC} = 5 V,$	Other input at 0 V	-0.8	-0.5		mA	
		$V_{I} = -7 V, V_{CC} = 0 V,$	Other input at 0 V	-0.8	-0.5			
	Current current	Driver dischlad	Outputs enabled			5		
I _{CC}	Supply current	Driver disabled	Outputs disabled			3	mA	

SWITCHING CHARACTERISTICS

 $V_{CC} = 5 V, T_A = 25^{\circ}C$

	PARAMETER	TEST COND	MIN	TYP	MAX	UNIT	
t _{PHL}	Propagation delay time, high- to low-level output			11	22	33	ns
t _{PLH}	Propagation delay time, low- to high-level output			11	22	33	ns
t _{sk(p)}	Pulse skew (t _{PHL} – t _{PLH})	$V_{ID} = -1.5 V$ to 1.5 V, See Figure 6			3	6	ns
t _t	Transition time				5	8	ns
t _{PZH}	Output enable time to high level					35	ns
t _{PZL}	Output enable time to low level					30	ns
t _{PHZ}	Output disable time from high level	See Figure 7				35	ns
t _{PLZ}	Output disable time from low level					30	ns

SWITCHING CHARACTERISTICS (SN55LBC180)

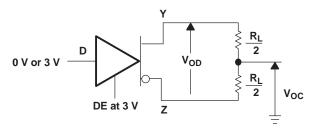
 $V_{CC} = 5 \text{ V}, \text{ } \text{T}_{A} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDIT	MIN TYP	MAX	UNIT	
t _{PHL}	Propagation delay time, high- to low-level output			26		ns
t _{PLH}	Propagation delay time, low- to high-level output	1 = 15 to 15		23		ns
t _{sk(p)}	Pulse skew (t _{PHL} – t _{PLH})	$V_{ID} = -1.5 V$ to 1.5 V, See Figure 6		3		ns
t _{sk(p)t}	Transition time			4		ns
t _{PZH}	Output enable time to high level			30		ns
t _{PHZ}	Output disable time from high level			26		ns
t _{PZL}	Output enable time to low level	See Figure 4		30		ns
t _{PLZ}	Output disable time from low level			30		ns

SLLS174G-FEBRUARY 1994-REVISED APRIL 2009



PARAMETER MEASUREMENT INFORMATION





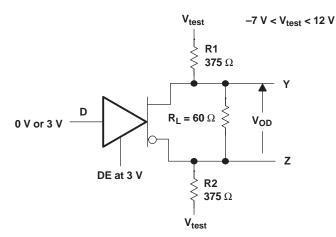
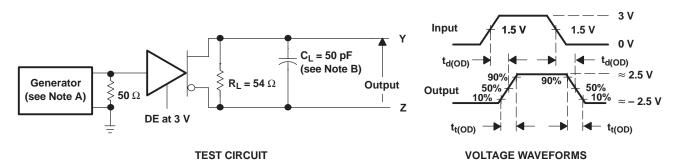


Figure 2. Driver V_{OD} Test Circuit

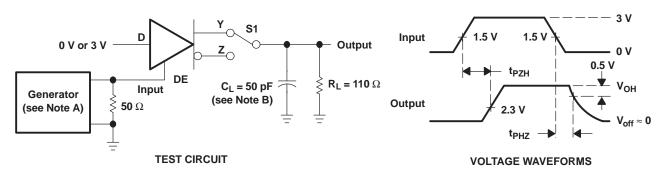


- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR > 1 MHz, 50% duty cycle, $t_r \le 6$ ns, $t_f \le 6$ ns, $Z_O = 50 \Omega$.
 - B. C_L includes probe and jig capacitance.

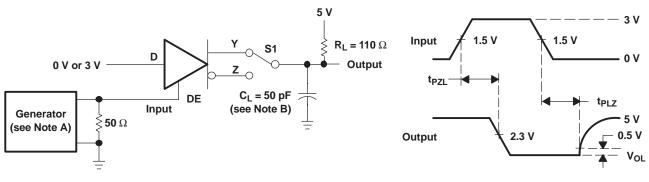
Figure 3. Driver Test Circuit and Differential Output Delay and Transition Time Voltage Waveforms







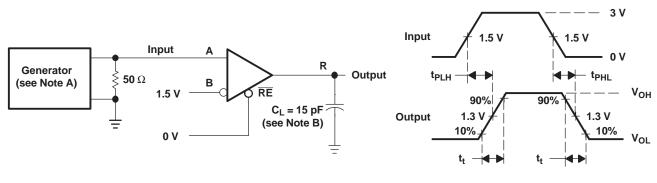




TEST CIRCUIT

VOLTAGE WAVEFORMS

Figure 5. Driver Test Circuit and Enable and Disable Time Voltage Waveforms



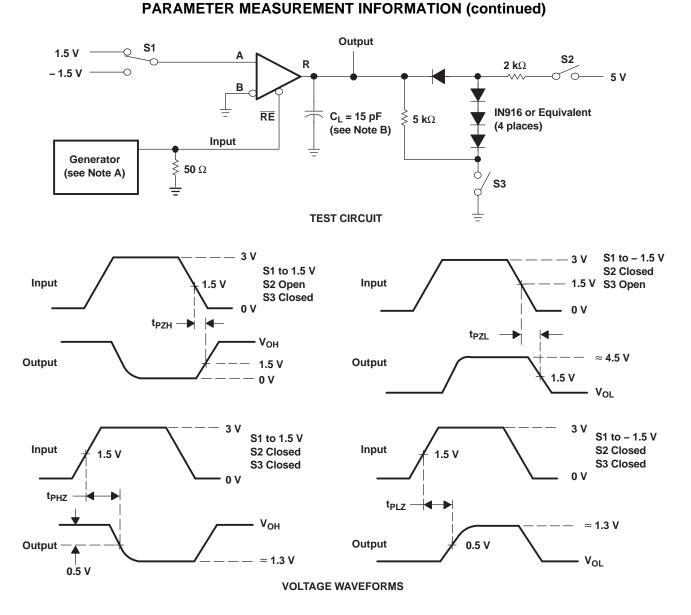
TEST CIRCUIT

VOLTAGE WAVEFORMS

- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, t_r \leq 6 ns, t_f \leq 6 ns, Z_O = 50 Ω .
 - B. C_L includes probe and jig capacitance.

Figure 6. Receiver Test Circuit and Propagation Delay Time Voltage Waveforms





NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, t_r \leq 6 ns, t_f \leq 6 ns, Z_O = 50 Ω .

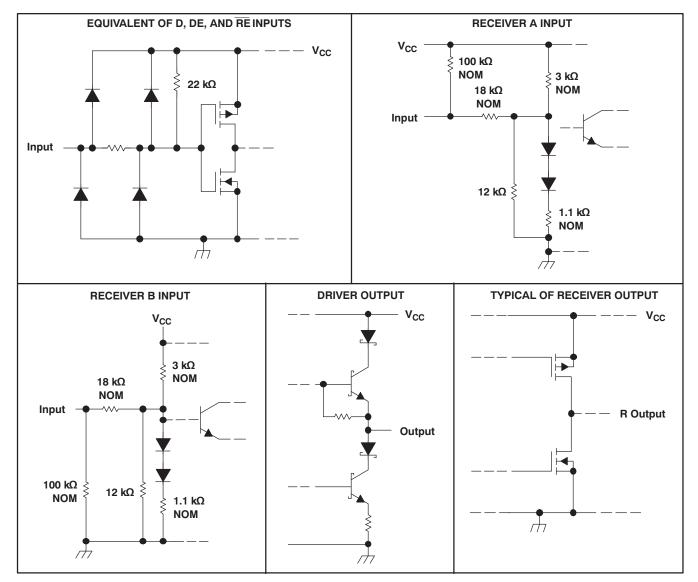
B. C_L includes probe and jig capacitance.

Figure 7. Receiver Output Enable and Disable Times



TYPICAL CHARACTERISTICS

SCHEMATICS OF INPUTS AND OUTPUTS

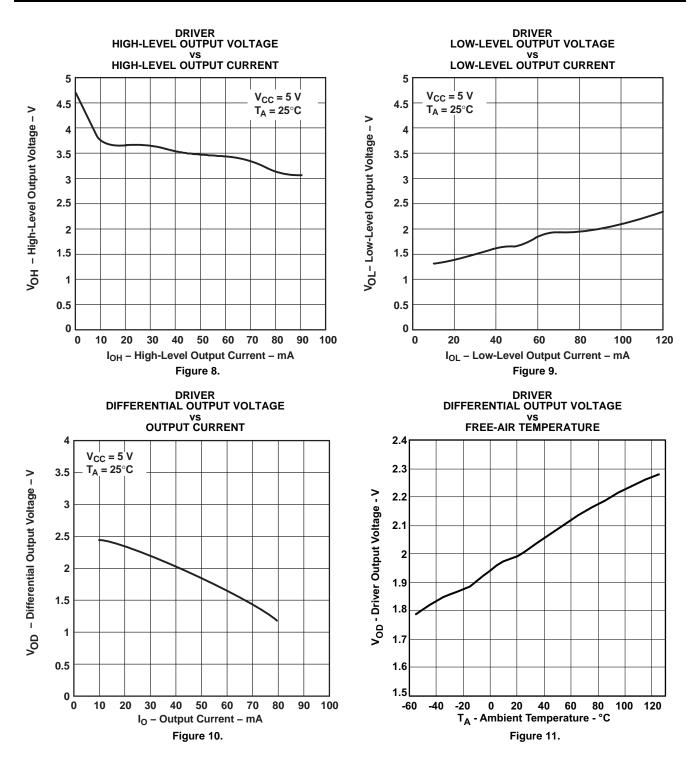


9

SN55LBC180 SN65LBC180 SN75LBC180 SLLS174G-FEBRUARY 1994-REVISED APRIL 2009

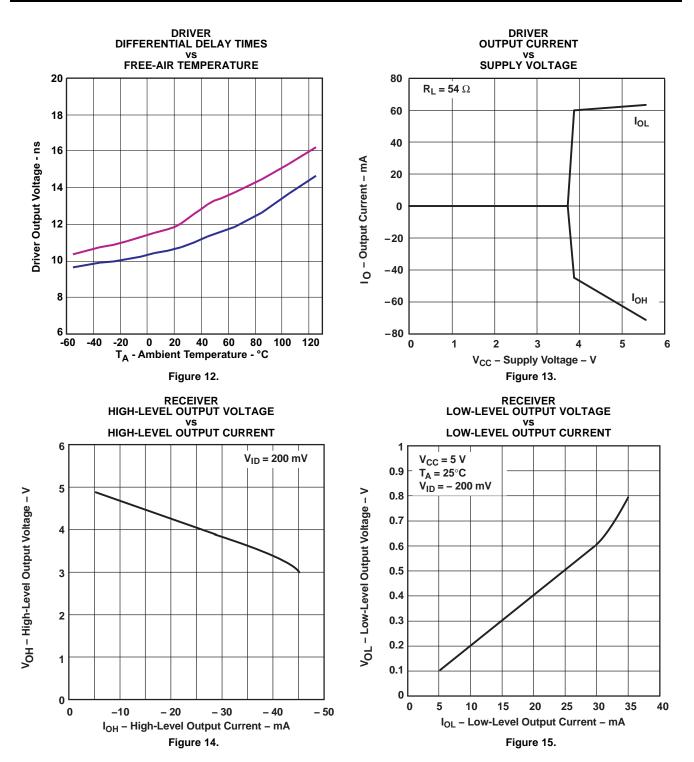


www.ti.com

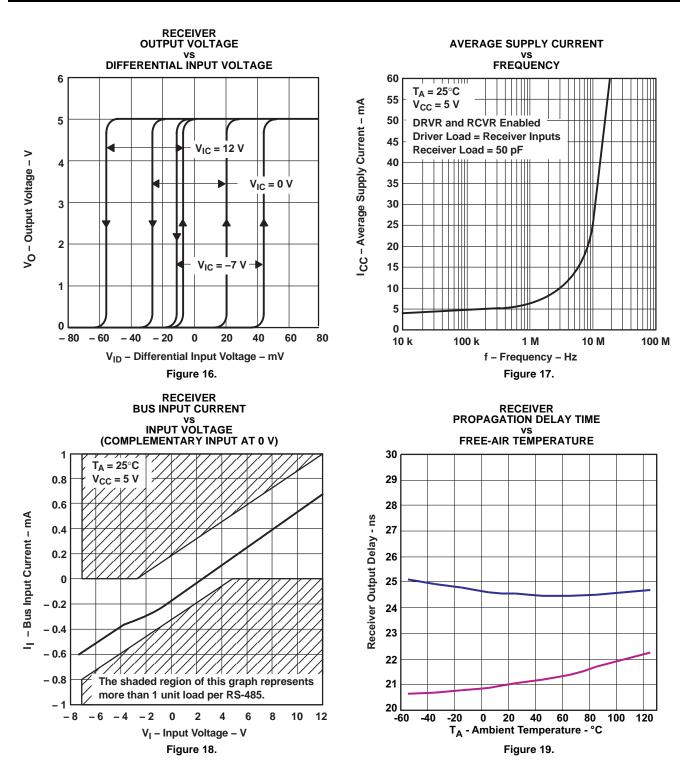




SN55LBC180 SN65LBC180 SN75LBC180 SLLS174G-FEBRUARY 1994-REVISED APRIL 2009









13

APPLICATION INFORMATION

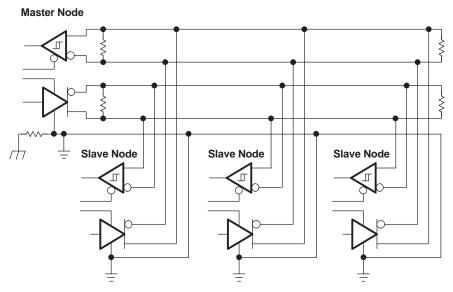


Figure 20. Full Duplex Application Circuit

17-Jul-2009

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN55LBC180RSAR	ACTIVE	QFN	RSA	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN55LBC180RSAT	ACTIVE	QFN	RSA	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LBC180D	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC180DG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC180DR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC180DRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LBC180N	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN65LBC180NE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN65LBC180RSAR	ACTIVE	QFN	RSA	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LBC180RSARG4	ACTIVE	QFN	RSA	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LBC180RSAT	ACTIVE	QFN	RSA	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LBC180RSATG4	ACTIVE	QFN	RSA	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN75LBC180D	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC180DG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC180DR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC180DRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75LBC180N	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75LBC180NE4	ACTIVE	PDIP	Ν	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
SN75LBC180RSAR	ACTIVE	QFN	RSA	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN75LBC180RSARG4	ACTIVE	QFN	RSA	16	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN75LBC180RSAT	ACTIVE	QFN	RSA	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN75LBC180RSATG4	ACTIVE	QFN	RSA	16	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.



17-Jul-2009

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN55LBC180, SN65LBC180, SN75LBC180 :

Automotive: SN65LBC180-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

www.ti.com

TAPE AND REEL INFORMATION

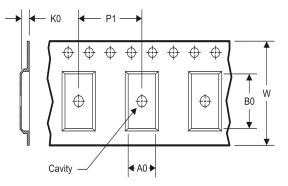
REEL DIMENSIONS

TEXAS INSTRUMENTS





TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN55LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN55LBC180RSAT	QFN	RSA	16	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN65LBC180DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN65LBC180RSAT	QFN	RSA	16	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN75LBC180DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN75LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN75LBC180RSAT	QFN	RSA	16	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

Texas Instruments

www.ti.com

PACKAGE MATERIALS INFORMATION

14-Jul-2012



*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN55LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0
SN55LBC180RSAT	QFN	RSA	16	250	210.0	185.0	35.0
SN65LBC180DR	SOIC	D	14	2500	333.2	345.9	28.6
SN65LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0
SN65LBC180RSAT	QFN	RSA	16	250	210.0	185.0	35.0
SN75LBC180DR	SOIC	D	14	2500	333.2	345.9	28.6
SN75LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0
SN75LBC180RSAT	QFN	RSA	16	250	210.0	185.0	35.0

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-leads (QFN) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-220.



RSA (S-PVQFN-N16)

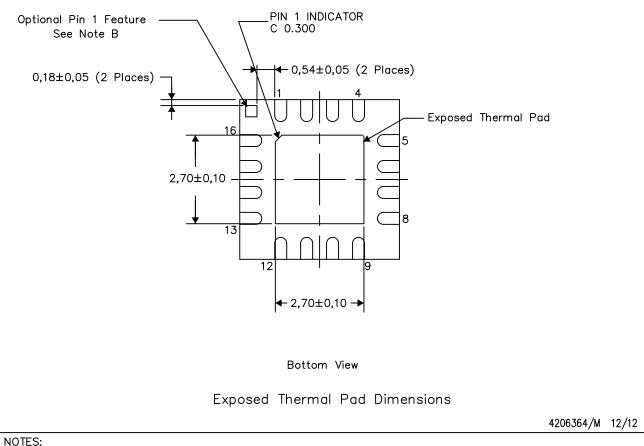
PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



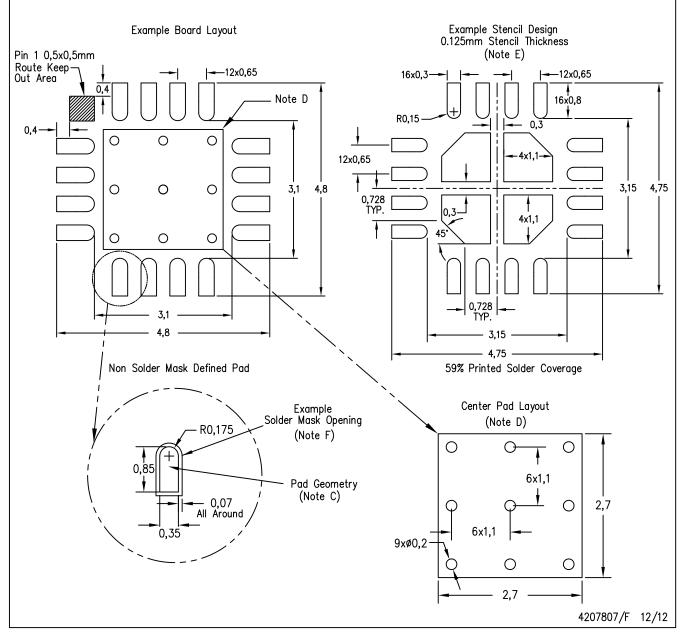
A. All linear dimensions are in millimeters

B. The Pin 1 Identification mark is an optional feature that may be present on some devices In addition, this Pin 1 feature if present is electrically connected to the center thermal pad and therefore should be considered when routing the board layout.



RSA (S-PVQFN-N16)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for solder mask tolerances.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconne	ectivity	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2013, Texas Instruments Incorporated